

Low-Voltage, Low-On-Resistance, SPST, CMOS Analog Switches

ABSOLUTE MAXIMUM RATINGS

(Voltages referenced to GND.)

V+-0.3V, +13V
Voltage into Any Terminal (Note 1).....	-0.3V to (V+ + 0.3V) or $\pm 20\text{mA}$ (whichever occurs first)
Continuous Current into Any Terminal.....	$\pm 20\text{mA}$
Peak Current, NO_ or COM_ $\pm 30\text{mA}$
(pulsed at 1ms, 10% duty cycle).....	
ESD per Method 3015.7	>2000V
Continuous Power Dissipation ($T_A = +70^\circ\text{C}$)	
8-Pin Plastic DIP (derate 9.09mW/ $^\circ\text{C}$ above $+70^\circ\text{C}$)	727mW
8-Pin SO (derate 5.88mW/ $^\circ\text{C}$ above $+70^\circ\text{C}$).....	471mW

5-Pin SOT23-5 (derate 7.1mW/ $^\circ\text{C}$ above $+70^\circ\text{C}$)	571mW
8-Pin Cerdip (derate 8.00mW/ $^\circ\text{C}$ above $+70^\circ\text{C}$).....	640mW
Operating Temperature Ranges	
MAX4514C_/_/MAX4515C_	0°C to $+70^\circ\text{C}$
MAX4514E_/_/MAX4515E_	-40°C to $+85^\circ\text{C}$
MAX4514MJA/MAX4515MJA	-55°C to $+125^\circ\text{C}$
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Lead Temperature (soldering, 10s)	$+300^\circ\text{C}$

Note 1: Voltages exceeding V+ or GND on any signal terminal are clamped by internal diodes. Limit forward-diode current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS—+5V Supply

(V+ = +4.5V to +5.5V, $V_{INH} = 2.4\text{V}$, $V_{INL} = 0.8\text{V}$, $T_A = T_{MIN}$ to T_{MAX} , unless otherwise noted. Typical values are at $T_A = +25^\circ\text{C}$.)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP (Note 2)	MAX	UNITS
ANALOG SWITCH							
Analog Signal Range	V_{COM}, V_{NO}, V_{NC}			0		V+	V
COM to NO or NC On-Resistance	R_{ON}	$V+ = 5V, V_{COM} = 3.5V, I_{COM} = 1mA$	$T_A = +25^{\circ}C$	10	20	Ω	
			$T_A = T_{MIN}$ to T_{MAX}	25			
COM to NO or NC On-Resistance Flatness	ΔR_{ON}	$V_{COM} = 1V, 2V, 3V; I_{COM} = 1mA$	$T_A = +25^{\circ}C$	1	3	Ω	
			$T_A = T_{MIN}$ to T_{MAX}	5			
NO or NC Off-Leakage Current (Note 3)	$I_{NO(OFF)}, I_{NC(OFF)}$	$V+ = 5.5V, V_{COM} = 1V, V_{NO}$ or $V_{NC} = 4.5V$	$T_A = +25^{\circ}C$	-1	0.01	1	nA
			$T_A = T_{MIN}$ to T_{MAX}	C, E	-20	20	
				M	-100	100	
COM Off-Leakage Current (Note 3)	$I_{COM(OFF)}$	$V+ = 5.5V, V_{COM} = 4.5V, V_{NO}$ or $V_{NC} = 1V$	$T_A = +25^{\circ}C$	-1	0.01	1	nA
			$T_A = T_{MIN}$ to T_{MAX}	C, E	-20	20	
				M	-100	100	
COM On-Leakage Current (Note 3)	$I_{COM(ON)}$	$V+ = 5.5V, V_{COM} = 4.5V, V_{NO}$ or $V_{NC} = 4.5V$	$T_A = +25^{\circ}C$	-2	0.01	2	nA
			$T_A = T_{MIN}$ to T_{MAX}	C, E	-40	40	
				M	-200	200	
DIGITAL I/O							
Input Logic High	V_{IH}			2.4		V+	V
Input Logic Low	V_{IL}			0		0.8	V
Input Current Logic High or Low	I_{IH}, I_{IL}	$V_{IN} = V+, 0V$		-1	0.03	1	μA
SWITCH DYNAMIC CHARACTERISTICS							
Turn-On Time	t_{ON}	Figure 2	$T_A = +25^{\circ}C$	30	150	ns	
			$T_A = T_{MIN}$ to T_{MAX}	240			
Turn-Off Time	t_{OFF}	Figure 2	$T_A = +25^{\circ}C$	20	100	ns	
			$T_A = T_{MIN}$ to T_{MAX}	150			

Low-Voltage, Low-On-Resistance, SPST, CMOS Analog Switches

MAX4514/MAX4515

ELECTRICAL CHARACTERISTICS—+5V Supply (continued)

(V+ = +4.5V to +5.5V, VINH = 2.4V, VINL = 0.8V, TA = TMIN to TMAX, unless otherwise noted. Typical values are at TA = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP (Note 2)	MAX	UNITS
SWITCH DYNAMIC CHARACTERISTICS						
Charge Injection (Note 4)	Q	CL = 1nF, VNO = 0V, RS = 0Ω, TA = +25°C, Figure 1		2	10	pC
Off Isolation	VISO	RL = 50Ω, CL = 15pF, VNO = 1VRMS, f = 100kHz, TA = +25°C, Figure 3		≤-90		dB
NO or NC Off Capacitance	CNO(OFF), CNC(OFF)	f = 1MHz, TA = +25°C, Figure 4		14		pF
COM Off Capacitance	CCOM(OFF)	f = 1MHz, TA = +25°C, Figure 4		14		pF
COM On Capacitance	CCOM(ON)	f = 1MHz, TA = +25°C, Figure 4		30		pF
POWER SUPPLY						
V+ Supply Current	I+	VIN = 0V or V+	TA = +25°C	-1	1	μA
			TA = TMIN to TMAX	-10	10	

ELECTRICAL CHARACTERISTICS—+12V Supply

(V+ = +11.4V to +12.6V, VINH = 5V, VINL = 0.8V, TA = TMIN to TMAX, unless otherwise noted. Typical values are at TA = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP (Note 2)	MAX	UNITS
ANALOG SWITCH						
Analog Signal Range	VCOM, VNO, VNC		0		V+	V
COM to NO or NC On-Resistance	RON	VCOM = 10V, ICOM = 1mA	TA = +25°C	5	10	Ω
			TA = TMIN to TMAX		15	
NO, NC Off-Leakage Current (Note 3)	I(NO)OFF I(NC)OFF	V+ = 12.6V, VCOM = 1V, VNO or VNC = 10V	TA = +25°C	-2	2	nA
			TA = TMIN to TMAX	C, E M	-50 -200	50 200
COM Off-Leakage Current (Note 3)	ICOM(OFF)	V+ = 12.6V, VCOM = 10V, VNO or VNC = 1V	TA = +25°C	-2	2	nA
			TA = TMIN to TMAX	C, E M	-50 -200	50 200
COM On-Leakage Current (Note 3)	ICOM(ON)	V+ = 12.6V, VCOM = 10V, VNO or VNC = 10V	TA = +25°C	-4	4	nA
			TA = TMIN to TMAX	C, E M	-100 -400	100 400
DIGITAL I/O						
Input Logic High	VINH		5		V+	V
Input Logic Low	VINL		0		0.8	V
Input Current Logic High or Low	IINH, IINL	VIN = V+, 0V	-1	0.03	1	μA
POWER SUPPLY						
V+ Supply Current	I+	IN = 0V or V+	TA = +25°C	-2	2	μA
			TA = TMIN to TMAX	-20	20	

Low-Voltage, Low-On-Resistance, SPST, CMOS Analog Switches

ELECTRICAL CHARACTERISTICS—+3V Supply

(V+ = +3V to +3.6V, T_A = T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at T_A = +25°C.)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP (Note 2)	MAX	UNITS
ANALOG SWITCH							
Analog Signal Range	V _{COM} , V _{NO} , V _{NC}			0		V+	V
COM to NO or NC On-Resistance	R _{ON}	V _{COM} = 1.5V, I _{NO} = 1mA, V+ = 3V	T _A = +25°C	20		50	Ω
			T _A = T _{MIN} to T _{MAX}			75	
DIGITAL I/O							
Input Logic High	V _{INH}			2.4		V+	V
Input Logic Low	V _{INL}			0		0.80	V
Input Current Logic High or Low	I _{INH} , I _{INL}	V _{IN} = V+, 0V		-1	0.03	1	μA
SWITCH DYNAMIC CHARACTERISTICS							
Turn-On Time (Note 4)	t _{ON}	Figure 2	T _A = +25°C	45		150	ns
			T _A = T _{MIN} to T _{MAX}			240	
Turn-Off Time (Note 4)	t _{OFF}	Figure 2	T _A = +25°C	30		100	ns
			T _A = T _{MIN} to T _{MAX}			150	
Charge Injection (Note 4)	Q	C _L = 1nF, Figure 1	T _A = +25°C	4		10	pC
POWER SUPPLY							
V+ Supply Current	I+	I _N = 0V or V+	T _A = +25°C	-1		1	μA
			T _A = T _{MIN} to T _{MAX}	-10		10	

Note 2: The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

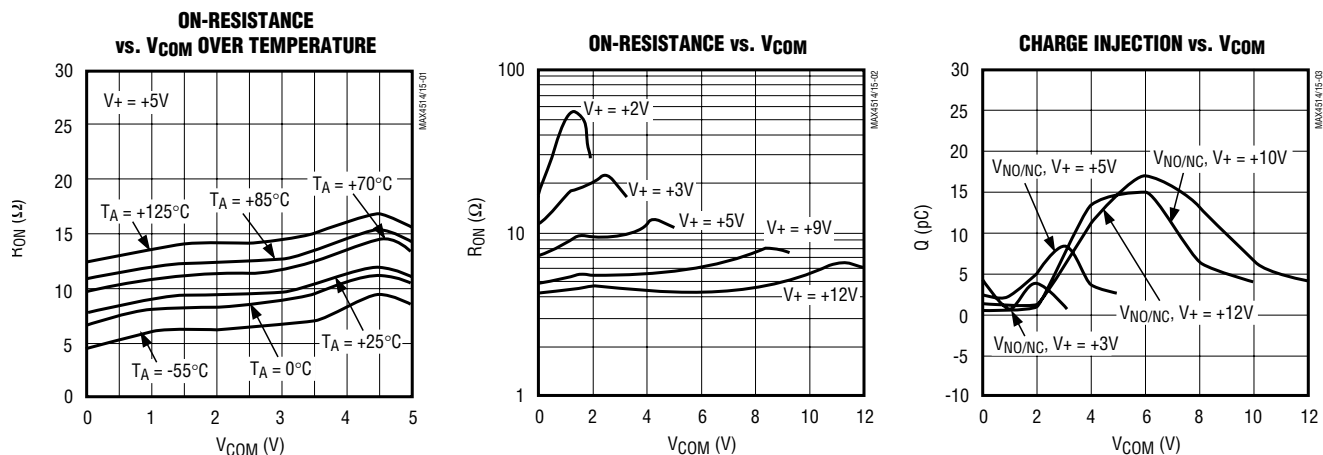
Note 3: Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are guaranteed by correlation at +25°C.

Note 4: Guaranteed, not production tested.

Note 5: SOT packaged parts are 100% tested at +25°C. Limits at maximum and minimum rated temperature are guaranteed by design and correlation limits at +25°C.

Typical Operating Characteristics

(V₊ = +5V, GND = 0V, T_A = +25°C, unless otherwise noted.)

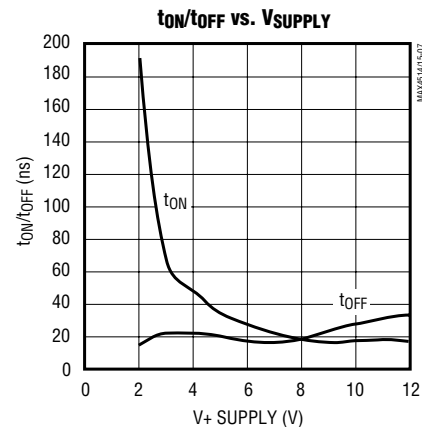
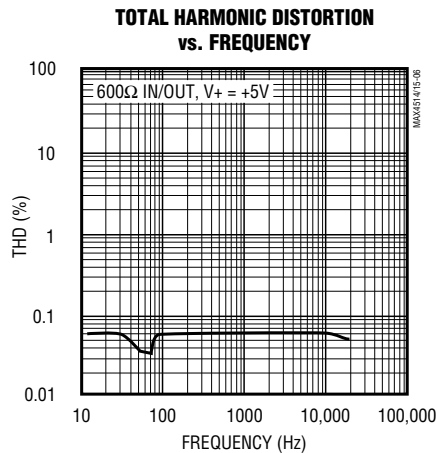
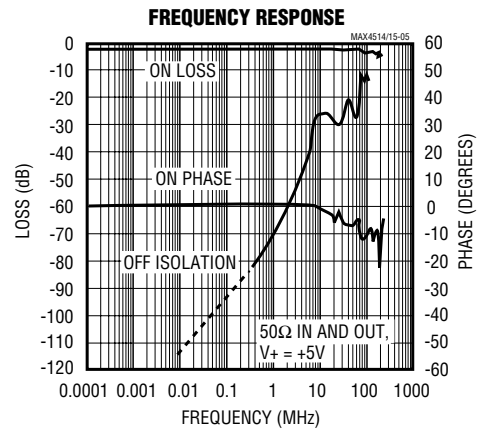
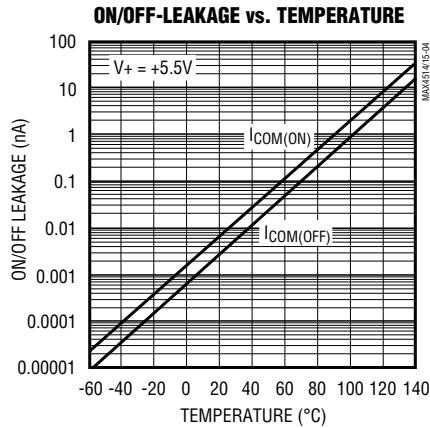


Low-Voltage, Low-On-Resistance, SPST, CMOS Analog Switches

MAX4514/MAX4515

Typical Operating Characteristics (continued)

(V+ = +5V, GND = 0V, T_A = +25°C, unless otherwise noted.)



Pin Description

PIN				NAME	FUNCTION
MAX4514		MAX4515			
DIP/SO	SOT23-5	DIP/SO	SOT23-5		
1	1	1	1	COM	Analog Switch Common Terminal
2, 3, 5	—	2, 3, 5	—	N.C.	No Connection (Not Internally Connected)
4	5	4	5	V+	Positive Supply-Voltage Input (Analog and Digital)
6	4	6	4	IN	Digital Control Input
7	3	7	3	GND	Ground
8	2	—	—	NO	Analog Switch (Normally Open)
—	—	8	2	NC	Analog Switch (Normally Cosed)

Note: NO, NC, and COM pins are identical and interchangeable. Any may be considered as an input or an output; signals pass equally well in both directions.

Low-Voltage, Low-On-Resistance, SPST, CMOS Analog Switches

Applications Information

Power-Supply Considerations

The MAX4514/MAX4515 construction is typical of most CMOS analog switches, except that they have only two supply pins: V+ and GND. V+ and GND drive the internal CMOS switches and set their analog voltage limits. Reverse ESD-protection diodes are internally connected between each analog-signal pin and both V+ and GND. One of these diodes conducts if any analog signal exceeds V+ or GND.

Virtually all the analog leakage current comes from the ESD diodes to V+ or GND. Although the ESD diodes on a given signal pin are identical and therefore fairly well balanced, they are reverse biased differently. Each is biased by either V+ or GND and the analog signal. This means their leakages will vary as the signal varies. The difference in the two diode leakages to the V+ and GND pins constitutes the analog-signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of the same or opposite polarity.

There is no connection between the analog-signal paths and V+ or GND.

V+ and GND also power the internal logic and logic-level translators. The logic-level translators convert the logic levels to switched V+ and GND signals to drive the analog signal gates.

Logic-Level Thresholds

The logic-level thresholds are CMOS/TTL compatible when V+ is +5V. As V+ is raised, the level threshold increases slightly. When V+ reaches +12V, the level threshold is about 3.0V—above the TTL guaranteed high-level minimum of 2.8V, but still compatible with CMOS outputs.

Do not connect the MAX4514/MAX4515's V+ to +3V and then connect the logic-level pins to logic-level signals that operate from +5V supply. Output levels can exceed +3V and violate the absolute maximum ratings, damaging the part and/or external circuits.

High-Frequency Performance

In 50Ω systems, signal response is reasonably flat up to 250MHz (see *Typical Operating Characteristics*). Above 20MHz, the on response has several minor peaks that are highly layout dependent. The problem is not in turning the switch on; it's in turning it off. The off-state switch acts like a capacitor and passes higher frequencies with less attenuation. At 10MHz, off isolation is about -45dB in 50Ω systems, decreasing (approximately 20dB per decade) as frequency increases. Higher circuit impedances also make off isolation decrease. Off isolation is about 3dB above that of a bare IC socket, and is due entirely to capacitive coupling.

Test Circuits/Timing Diagrams

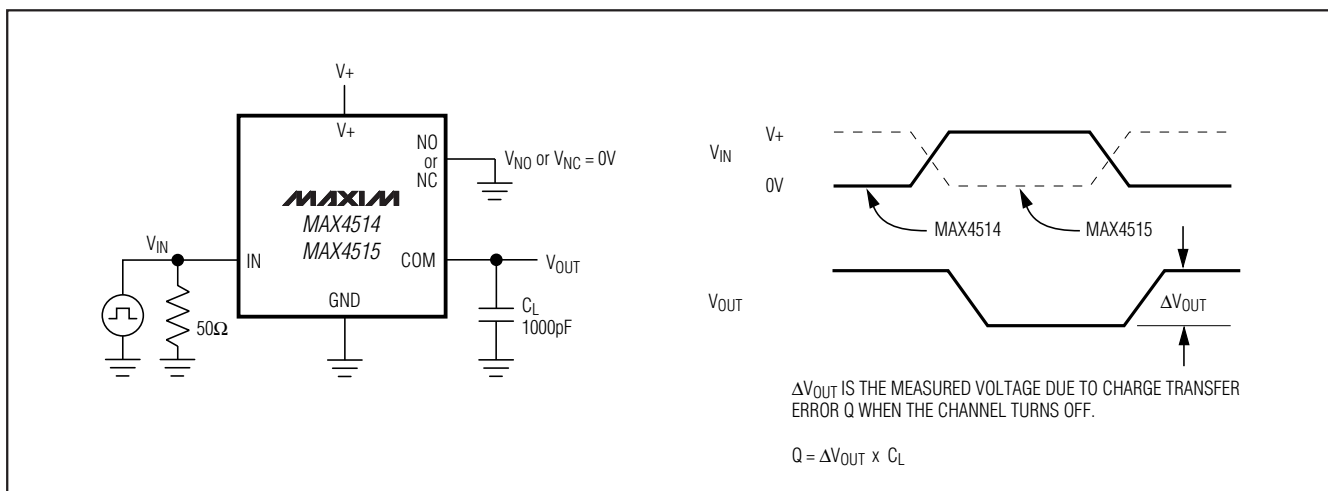


Figure 1. Charge Injection

Low-Voltage, Low-On-Resistance, SPST, CMOS Analog Switches

Test Circuits/Timing Diagrams (continued)

MAX4514/MAX4515

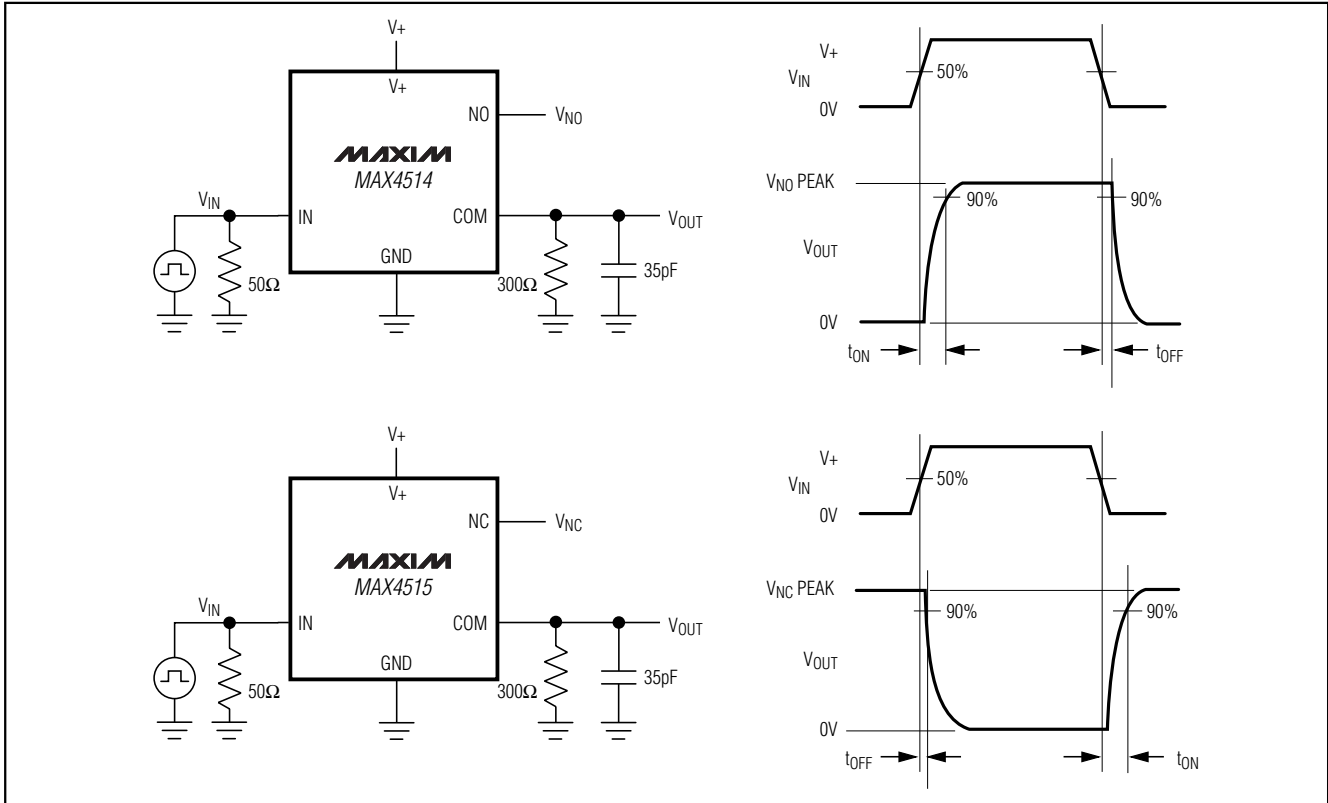


Figure 2. Switching Times

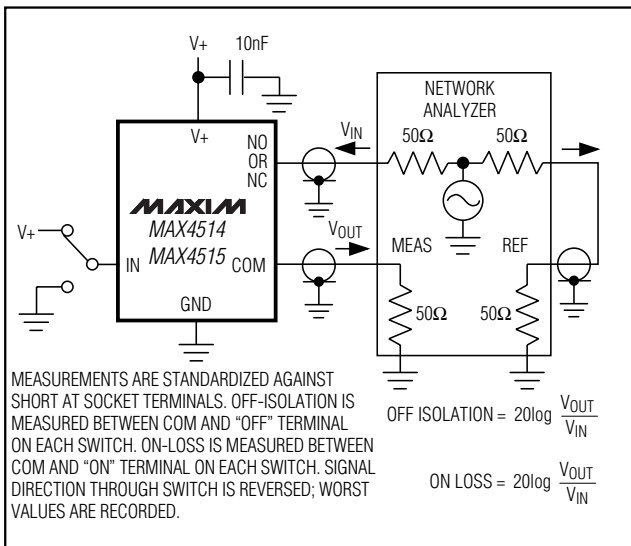


Figure 3. Off-Isolation and On-Loss

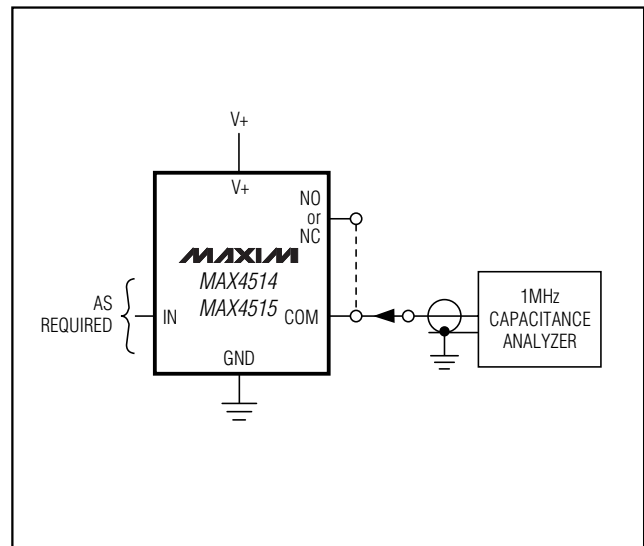


Figure 4. NO, NC, and COM Capacitance

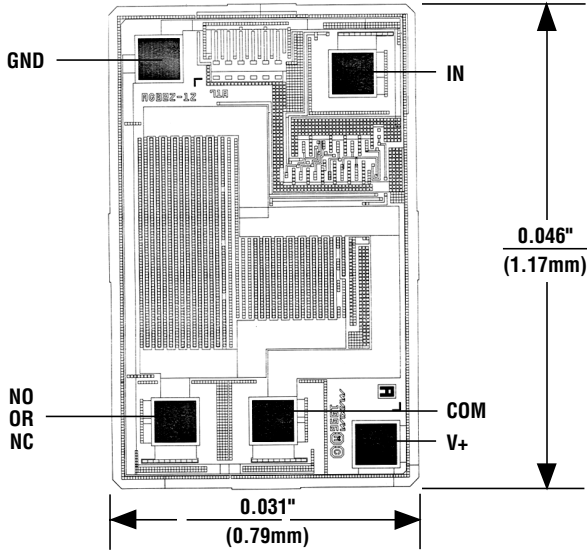
Low-Voltage, Low-On-Resistance,
SPST, CMOS Analog Switches

Ordering Information (continued)

PART	TEMP. RANGE	PIN-PACKAGE
MAX4514EPA	-40°C to +85°C	8 Plastic DIP
MAX4514ESA	-40°C to +85°C	8 SO
MAX4514EUK	-40°C to +85°C	5 SOT23-5
MAX4514MJA	-55°C to +125°C	8 Cerdip**
MAX4515CPA	0°C to +70°C	8 Plastic DIP
MAX4515CSA	0°C to +70°C	8 SO
MAX4515CUK	0°C to +70°C	5 SOT23-5
MAX4515C/D	0°C to +70°C	Dice*
MAX4515EPA	-40°C to +85°C	8 Plastic DIP
MAX4515ESA	-40°C to +85°C	8 SO
MAX4515EUK	-40°C to +85°C	5 SOT23-5
MAX4515MJA	-55°C to +125°C	8 Cerdip**

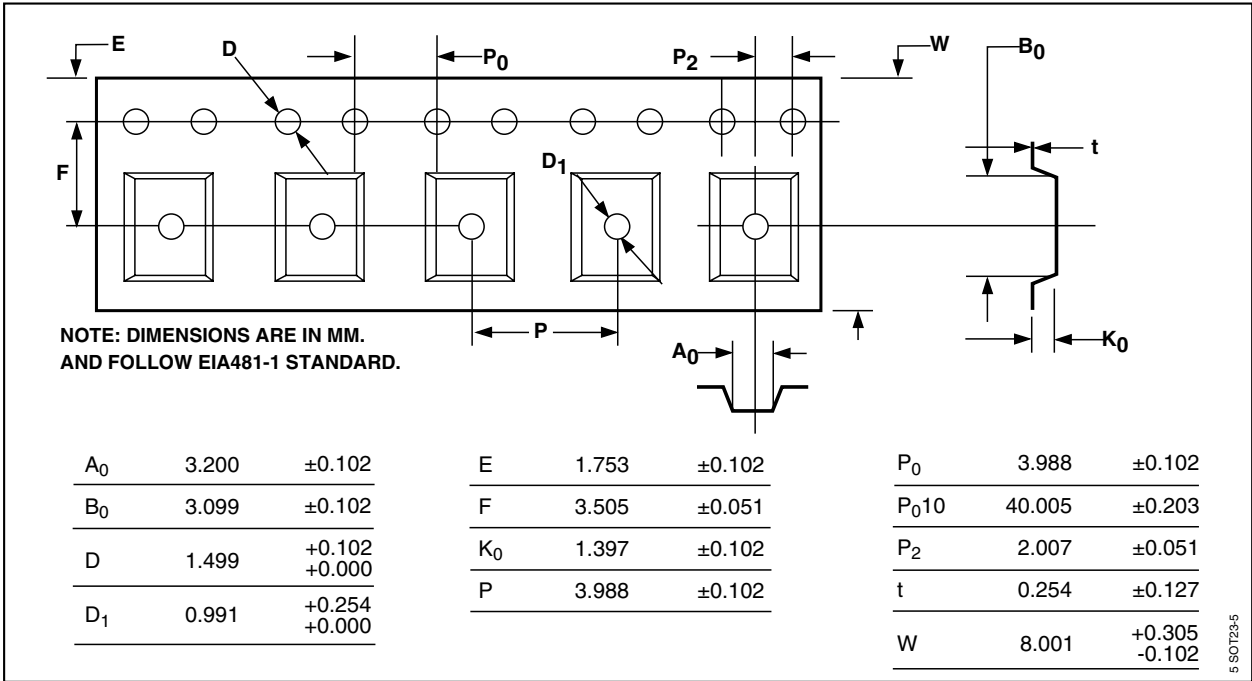
*Contact factory for dice specifications.
**Contact factory for availability.

Chip Topography



TRANSISTOR COUNT: 19
SUBSTRATE IS INTERNALLY CONNECTED TO V+

Tape-and-Reel Information



Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

8 Maxim Integrated Products, 120 San Gabriel Drive, Sunnyvale, CA 94086 (408) 737-7600

© 2005 Maxim Integrated Products Printed USA MAXIM is a registered trademark of Maxim Integrated Products, Inc.